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Understanding **Embedded - FPGAs (Field Programmable Gate Array)**



Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	109000
Total RAM Bits	7782400
Number of I/O	170
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	325-LFBGA, FCBGA
Supplier Device Package	325-FCBGA (11x11)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf100t-fcsg325e

Table 8 • Maximum Overshoot During Transitions for GPIO

AC (V_{IN}) Overshoot Duration as % at $T_J = 100^\circ C$	Condition (V)
100	3.8
100	3.85
100	3.9
100	3.95
70	4
50	4.05
33	4.1
22	4.15
14	4.2
9.8	4.25
6.5	4.3
4.4	4.35
3	4.4
2	4.45
1.4	4.5
0.9	4.55
0.6	4.6

Note: Overshoot level is for V_{DDI} at 3.3 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for GPIO.

Table 9 • Maximum Undershoot During Transitions for GPIO

AC (V_{IN}) Undershoot Duration as % at $T_J = 100^\circ C$	Condition (V)
100	-0.5
100	-0.55
100	-0.6
100	-0.65
100	-0.7
100	-0.75
100	-0.8
100	-0.85
100	-0.9
100	-0.95
100	-1
100	-1.05
100	-1.1
100	-1.15
100	-1.2
69	-1.25
45	-1.3

Note: The following dedicated pins do not support hot socketing: TMS, TDI, TRSTB, DEVRST_N, and FF_EXIT_N. Weak pull-up (as specified in GPIO) is always enabled.

6.3 Input and Output

The following section describes:

- DC I/O levels
- Differential and complementary differential DC I/O levels
- HSIO and GPIO on-die termination specifications
- LVDS specifications

6.3.1 DC Input and Output Levels

The following tables list the DC I/O levels.

Table 12 • DC Input Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{IL} Min (V)	V _{IL} Max (V)	V _{IH} Min (V)	V _{IH} ¹ Max (V)
PCI	3.15	3.3	3.45	-0.3	0.3 x V _{DDI}	0.5 x V _{DDI}	3.45
LVTTL	3.15	3.3	3.45	-0.3	0.8	2	3.45
LVCMOS33	3.15	3.3	3.45	-0.3	0.8	2	3.45
LVCMOS25	2.375	2.5	2.625	-0.3	0.7	1.7	2.625
LVCMOS18	1.71	1.8	1.89	-0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.89
LVCMOS15	1.425	1.5	1.575	-0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.575
LVCMOS12	1.14	1.2	1.26	-0.3	0.35 x V _{DDI}	0.65 x V _{DDI}	1.26
SSTL25I ²	2.375	2.5	2.625	-0.3	V _{REF} - 0.15	V _{REF} + 0.15	2.625
SSTL25II ²	2.375	2.5	2.625	-0.3	V _{REF} - 0.15	V _{REF} + 0.15	2.625
SSTL18I ²	1.71	1.8	1.89	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	1.89
SSTL18II ²	1.71	1.8	1.89	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	1.89
SSTL15I	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575
SSTL15II	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575

Table 13 • DC Output Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL^{2,6}} mA	I _{OH^{2,6}} mA
PCI ¹	3.15	3.3	3.45		0.1 x V _{DDI}	0.9 x V _{DDI}		1.5	0.5
LVTTL	3.15	3.3	3.45		0.4	2.4			
LVCMOS33	3.15	3.3	3.45		0.4	V _{DDI} — 0.4			
LVCMOS25	2.375	2.5	2.625		0.4	V _{DDI} — 0.4			
LVCMOS18	1.71	1.8	1.89		0.45	V _{DDI} — 0.45			
LVCMOS15	1.425	1.5	1.575		0.25 x V _{DDI}	0.75 x V _{DDI}			
LVCMOS12	1.14	1.2	1.26		0.25 x V _{DDI}	0.75 x V _{DDI}			
SSTL25I ³	2.375	2.5	2.625		V _{TT} — 0.608	V _{TT} + 0.608	8.1	8.1	
SSTL25II ³	2.375	2.5	2.625		V _{TT} — 0.810	V _{TT} + 0.810	16.2	16.2	
SSTL18I ³	1.71	1.8	1.89		V _{TT} — 0.603	V _{TT} + 0.603	6.7	6.7	
SSTL18II ³	1.71	1.8	1.89		V _{TT} — 0.603	V _{TT} + 0.603	13.4	13.4	
SSTL15I ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}	V _{OL} /40 (V _{DDI} – V _{OH}) /40		
SSTL15II ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}	V _{OL} /34 (V _{DDI} – V _{OH}) /34		
SSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}	V _{OL} /40 (V _{DDI} – V _{OH}) /40		
SSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}	V _{OL} /34 (V _{DDI} – V _{OH}) /34		
HSTL15I	1.425	1.5	1.575		0.4	V _{DDI} — 0.4	8	8	
HSTL15II	1.425	1.5	1.575		0.4	V _{DDI} — 0.4	16	16	

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
HSTL135I ⁴	1.283	1.35	1.418	0.2 x V _{DDI}	0.8 x V _{DDI}			V _{OL} /50 /50	(V _{DDI} – V _{OH}) /50
HSTL135II ⁴	1.283	1.35	1.418	0.2 x V _{DDI}	0.8 x V _{DDI}			V _{OL} /25 /25	(V _{DDI} – V _{OH}) /25
HSTL12I ⁴	1.14	1.2	1.26	0.1 x V _{DDI}	0.9 x V _{DDI}			V _{OL} /50 /50	(V _{DDI} – V _{OH}) /50
HSTL12II ⁴	1.14	1.2	1.26	0.1 x V _{DDI}	0.9 x V _{DDI}			V _{OL} /25 /25	(V _{DDI} – V _{OH}) /25
HSUL18I ⁴	1.71	1.8	1.89	0.1 x V _{DDI}	0.9 x V _{DDI}			V _{OL} /55 /55	(V _{DDI} – V _{OH}) /55
HSUL18II ⁴	1.71	1.8	1.89	0.1 x V _{DDI}	0.9 x V _{DDI}			V _{OL} /25 /25	(V _{DDI} – V _{OH}) /25
HSUL12I ⁴	1.14	1.2	1.26	0.1 x V _{DDI}	0.9 x V _{DDI}			V _{OL} /40 /40	(V _{DDI} – V _{OH}) /40
POD12I ^{4,5}	1.14	1.2	1.26	0.5 x V _{DDI}				V _{OL} /48 /48	(V _{DDI} – V _{OH}) /48
POD12II ^{4,5}	1.14	1.2	1.26	0.5 x V _{DDI}				V _{OL} /34 /34	(V _{DDI} – V _{OH}) /34

1. Drive strengths per PCI specification V/I curves.
2. Refer to [UG0686: PolarFire FPGA User I/O User Guide](#) for details on supported drive strengths.
3. For external stub-series resistance. This resistance is on-die for GPIO.
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).
5. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
6. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

6.3.2 Differential DC Input and Output Levels

The follow tables list the differential DC I/O levels.

Table 14 • Differential DC Input Levels

I/O Standard	Bank Type	V _{ICM_RANGE} Libero Setting	V _{ICM^{1,3}} Min (V)	V _{ICM^{1,3}} Typ (V)	V _{ICM^{1,3}} Max (V)	V _{ID²} Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
LVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS18 ⁴	GPIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6

Standard	Description	V _L ¹	V _H ¹	V _{ID} ²	V _{ICM} ²	V _{MEAS} ^{3,4}	V _{REF} ^{1,5}	Unit
SLVS25	SLVS 2.5 V	V _{ICM} – .125	V _{ICM} + .125	0.250	0.200	0		V
SLVS18	SLVS 1.8 V	V _{ICM} – .125	V _{ICM} + .125	0.250	0.200	0		V
HCSL33	High-speed current steering logic (HCSL) 3.3 V	V _{ICM} – .125	V _{ICM} + .125	0.250	0.350	0		V
HCSL25	HCSL 2.5 V	V _{ICM} – .125	V _{ICM} + .125	0.250	0.350	0		V
HCSL18	HCSL 1.8 V	V _{ICM} – .125	V _{ICM} + .125	0.250	0.350	0		V
BLVDSE25 ⁶	Bus LVDS 2.5 V	V _{ICM} – .125	V _{ICM} + .125	0.250	1.250	0		V
MLVDSE25 ⁶	Multipoint LVDS 2.5 V	V _{ICM} – .125	V _{ICM} + .125	0.250	1.250	0		V
LVPECL33	Low-voltage positive emitter coupled logic	V _{ICM} – .125	V _{ICM} + .125	0.250	1.650	0		V
LVPECLE33 ⁶	Low-voltage positive emitter coupled logic	V _{ICM} – .125	V _{ICM} + .125	0.250	1.650	0		V
SSTL25I	Differential SSTL 2.5 V Class I	V _{ICM} – .125	V _{ICM} + .125	0.250	1.250	0		V
SSTL25II	Differential SSTL 2.5 V Class II	V _{ICM} – .125	V _{ICM} + .125	0.250	1.250	0		V
SSTL18I	Differential SSTL 1.8 V Class I	V _{ICM} – .125	V _{ICM} + .125	0.250	0.900	0		V
SSTL18II	Differential SSTL 1.8 V Class II	V _{ICM} – .125	V _{ICM} + .125	0.250	0.900	0		V
SSTL15	Differential SSTL 1.5 V Class I	V _{ICM} – .125	V _{ICM} + .125	0.250	0.750	0		V
SSTL135	Differential SSTL 1.5 V Class II	V _{ICM} – .125	V _{ICM} + .125	0.250	0.750	0		V
HSTL15I	Differential HSTL 1.5 V Class I	V _{ICM} – .125	V _{ICM} + .125	0.250	0.750	0		V
HSTL15II	Differential HSTL 1.5 V Class II	V _{ICM} – .125	V _{ICM} + .125	0.250	0.750	0		V
HSTL135I	Differential HSTL 1.35 V Class I	V _{ICM} – .125	V _{ICM} + .125	0.250	0.675	0		V

Standard	Description	V _L ¹	V _H ¹	V _{ID} ²	V _{ICM} ²	V _{MEAS} ^{3, 4}	V _{REF} ^{1, 5}	Unit
HSTL135II	Differential HSTL 1.35 V Class II	V _{ICM} – .125	V _{ICM} + .125	0.250	0.675	0		V
HSTL12	Differential HSTL 1.2 V	V _{ICM} – .125	V _{ICM} + .125	0.250	0.600	0		V
HSUL18I	Differential HSUL 1.8 V Class I	V _{ICM} – .125	V _{ICM} + .125	0.250	0.900	0		V
HSUL18II	Differential HSUL 1.8 V Class II	V _{ICM} – .125	V _{ICM} + .125	0.250	0.900	0		V
HSUL12	Differential HSUL 1.2 V	V _{ICM} – .125	V _{ICM} + .125	0.250	0.600	0		V
POD12I	Differential POD 1.2 V Class I	V _{ICM} – .125	V _{ICM} + .125	0.250	0.600	0		V
POD12II	Differential POD 1.2 V Class II	V _{ICM} – .125	V _{ICM} + .125	0.250	0.600	0		V
MIPI25	Mobile Industry Processor Interface	V _{ICM} – .125	V _{ICM} + .125	0.250	0.200	0		V

1. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst-case of these measurements. V_{REF} values listed are typical. Input waveform switches between V_L and V_H. All rise and fall times must be 1 V/ns.
2. Differential receiver standards all use 250 mV V_{ID} for timing. V_{CM} is different between different standards.
3. Input voltage level from which measurement starts.
4. The value given is the differential input voltage.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models or shown in [Output Delay Measurement—Single-Ended Test Setup \(see page 27\)](#).
6. Emulated bi-directional interface.

7.1.2 Output Delay Measurement Methodology

The following section provides information about the methodology for output delay measurement.

Table 23 • Output Delay Measurement Methodology

Standard	Description	R _{REF} (Ω)	C _{REF} (pF)	V _{MEAS} (V)	V _{REF} (V)
PCI	PCIE 3.3 V	25	10	1.65	
LVTTL33	LVTTL 3.3 V	1M	0	1.65	
LVCMOS33	LVCMOS 3.3 V	1M	0	1.65	
LVCMOS25	LVCMOS 2.5 V	1M	0	1.25	
LVCMOS18	LVCMOS 1.8 V	1M	0	0.90	
LVCMOS15	LVCMOS 1.5 V	1M	0	0.75	
LVCMOS12	LVCMOS 1.2 V	1M	0	0.60	
SSTL25I	Stub-series terminated logic 2.5 V Class I	50	0	V _{REF}	1.25
SSTL25II	SSTL 2.5 V Class II	50	0	V _{REF}	1.25

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Clock-to- Data Condition
F_{MAX} 4:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F_{MAX} 8:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F_{MAX} 2:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F_{MAX} 4:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F_{MAX} 8:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F_{MAX} 2:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F_{MAX} 4:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F_{MAX} 8:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F_{MAX} 2:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F_{MAX} 4:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Clock-to- Data Condition
F_{MAX} 8:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Table 32 • I/O Digital Transmit Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Forwarded Clock-to-Data Skew
Output F_{MAX}	TX_SDR_G_A	Tx SDR							MHz	From a global clock source, aligned ¹
	TX_SDR_G_C	Tx SDR							MHz	From a global clock source, centered ¹

1. A centered clock-to-data interface can be created with a negedge launch of the data.

Table 33 • I/O Digital Transmit Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Forwarded Clock-to- Data Skew
Output F_{MAX}	TX_DDR_G_A	Tx DDR			335			335	MHz	From a global clock source, aligned
	TX_DDR_G_C	Tx DDR			335			335	MHz	From a global clock source, centered
	TX_DDR_L_A	Tx DDR			250			250	MHz	From a lane clock source, aligned
	TX_DDR_L_C	Tx DDR			250			250	MHz	From a lane clock source, centered
Output F_{MAX} 2:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output F_{MAX} 4:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output F_{MAX} 8:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Forwarded Clock-to-Data Skew
Output F_{MAX} 2:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F_{MAX} 4:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F_{MAX} 8:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
In delay, out delay, DLL delay step sizes			12.7	30	35	12.7	25	29.5	ps	

Table 34 • I/O CDR Switching Characteristics

Parameter	Min	Max	Unit
Data rate	266	1250	Mbps
Receiver Sinusoidal jitter tolerance ¹	0.2		UI

1. Jitter values based on bit error ratio (BER) of 10–12, 80 MHz sinusoidal jitter injected to Rx data.

Note: See the LVDS output buffer specifications for transmit characteristics.

7.2 Clocking Specifications

This section describes the PLL and DLL clocking and oscillator specifications.

7.2.1 Clocking

The following table provides clocking specifications.

Table 35 • Global and Regional Clock Characteristics (−40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Global clock F_{MAX}	F_{MAXG}	500	500	500	500	MHz	
Regional clock F_{MAX}	F_{MAXR}	375	375	375	375	MHz	Transceiver interfaces only
	F_{MAXR}	250	250	250	250	MHz	All other interfaces
Global clock duty cycle distortion	T_{DCDG}	190	190	190	190	ps	At 500 MHz

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Regional clock duty cycle distortion	T _{DCDR}	120	120	120	120	ps	At 250 MHz

The following table provides clocking specifications from –40 °C to 100 °C.

Table 36 • High-Speed I/O Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
High-speed I/O clock F _{MAX}	F _{MAXB}	1000	1250	1000	1250	MHz	HSIO and GPIO
High-speed I/O clock skew ¹	F _{SKEWB}	30	20	30	20	ps	HSIO without bridging
	F _{SKEWB}	600	500	600	500	ps	HSIO with bridging
	F _{SKEWB}	45	35	45	35	ps	GPIO without bridging
	F _{SKEWB}	75	60	75	60	ps	GPIO with bridging
High-speed I/O clock duty cycle distortion ²	T _{DCB}	90	90	90	90	ps	HSIO without bridging
	T _{DCB}	115	115	115	115	ps	HSIO with bridging
	T _{DCB}	90	90	90	90	ps	GPIO without bridging
	T _{DCB}	115	115	115	115	ps	GPIO with bridging

1. F_{SKEWB} is the worst-case clock-tree skew observable between sequential I/O elements. Clock-tree skew is significantly smaller at I/O registers close to each other and fed by the same or adjacent clock-tree branches. Use the Microsemi Timing Analyzer tool to evaluate clock skew specific to the design.
2. Parameters listed in this table correspond to the worst-case duty cycle distortion observable at the I/O flip flops. IBIS should be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times for any I/O standard.

7.2.2 PLL

The following table provides information about PLL.

Table 37 • PLL Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input clock frequency (integer mode)	F _{INI}	1		1250	MHz
Input clock frequency (fractional mode)	F _{INF}	10		1250	MHz
Minimum reference or feedback pulse width ¹	F _{IMPULSE}	200			ps
Frequency at the Frequency Phase Detector (PFD) (integer mode)	F _{PHDETI}	1		312	MHz
Frequency at the PFD (fractional mode)	F _{PHDETF}	10	50	125	MHz
Allowable input duty cycle	F _{INDUTY}	25		75	%

Parameter ¹	Symbol	Min	Typ	Max	Unit
Secondary output clock frequency ²	F _{OUTSF}	33.3		800	MHz
Input clock cycle-to-cycle jitter	F _{JIN}			200	ps
Output clock period cycle-to-cycle jitter (w/clean input)	T _{OUTJITTERP}			300	ps
Output clock-to-clock skew between two outputs with the same phase settings	T _{SKEW}			±200	ps
DLL lock time	T _{LOCK}	16		16K	Reference clock cycles
Minimum reset pulse width	T _{MRPW}	3			ns
Minimum input pulse width ³	T _{MIPW}	20			ns
Minimum input clock pulse width high	T _{MPWH}	400			ps
Minimum input clock pulse width low	T _{MPWL}	400			ps
Delay step size	T _{DEL}	12.7	30	35	ps
Maximum delay block delay ⁴	T _{DELMAX}	1.8		4.8	ns
Output clock duty cycle (with 50% duty cycle input) ⁵	T _{DUTY}	40		60	%
Output clock duty cycle (in phase reference mode) ⁵	T _{DUTYS0}	45		55	%

1. For all DLL modes.
2. Secondary output clock divided by four option.
3. On load, direction, move, hold, and update input signals.
4. 128 delay taps in one delay block.
5. Without duty cycle correction enabled.

7.2.4 RC Oscillators

The following tables provide internal RC clock resources for user designs and additional information about designing systems with RF front end information about emitters generated on-chip to support programming operations.

Table 39 • 2 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{2FREQ}		2		MHz
Accuracy	RC _{2FACC}	-4		4	%
Duty cycle	RC _{2DC}	46		54	%
Peak-to-peak output period jitter	RC _{2PJIT}	5	10		ns
Peak-to-peak output cycle-to-cycle jitter	RC _{2CJIT}	5	10		ns
Operating current (V _{DD2S})	RC _{2IVPPA}			60	µA
Operating current (V _{DD})	RC _{2IVDD}			2.6	µA

Table 40 • 160 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{SCFREQ}		160		MHz
Accuracy	RC _{SCFACC}	-4		4	%
Duty cycle	RC _{SCDC}	47		52	%
Peak-to-peak output period jitter	RC _{SCPJIT}			600	ps
Peak-to-peak output cycle-to-cycle jitter	RC _{SCCJIT}			172	ps
Operating current (V _{DD2S})	RC _{SCVPPA}			599	µA

7.3.2 SRAM Blocks

The following tables describe the LSRAM blocks' performance.

Table 43 • LSRAM Performance Industrial Temperature Range (−40 °C to 100 °C)

Parameter	V _{DD} = 1.0 V – STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V – STD	V _{DD} = 1.05 V – 1	Unit	Condition
Operating frequency	343	428	343	428	MHz	Two-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Two-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Dual-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Dual-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, pipelined, simple-write, and write-feed-through
	279	295	279	295	MHz	Two-port non-pipelined ECC mode, pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	196	285	196	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	274	285	274	285	MHz	Two-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port non-pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, non-pipelined, and read-before-write
	193	285	193	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, and read-before-write

Table 55 • PCI Express Gen2

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps	0.35		UI
Receiver jitter tolerance	5.0 Gbps	0.4		UI

Note: With add-in card as specified in PCI Express CEM Rev 2.0.

7.5.2 Interlaken

The following table describes Interlaken.

Table 56 • Interlaken

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	6.375 Gbps	0.3		UI
	10.3125 Gbps	0.3		UI
	12.7 Gbps ¹			UI
Receiver jitter tolerance	6.375 Gbps	0.6		UI
	10.3125 Gbps	0.65		UI
	12.7 Gbps ¹			UI

- For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions \(see page 6\)](#).

7.5.3 10GbE (10GBASE-R, and 10GBASE-KR)

The following table describes 10GbE (10GBASE-R).

Table 57 • 10GbE (10GBASE-R)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps	0.28		UI
Receiver jitter tolerance	10.3125 Gbps	0.7		UI

The following table describes 10GbE (10GBASE-KR).

Table 58 • 10GbE (10GBASE-KR)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps			UI
Receiver jitter tolerance	10.3125 Gbps			UI

The following table describes 10GbE (XAUI).

Table 59 • 10GbE (XAUI)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter (near end)	3.125 Gbps	0.35		UI
Total transmit jitter (far end)		0.55		UI
Receiver jitter tolerance	3.125 Gbps	0.65		UI

The following table describes 10GbE (RXAUI).

Table 60 • 10GbE (RXAUI)

	Data Rate	Min	Max	Unit
Total transmit jitter	6.25 Gbps			UI
Receiver jitter tolerance	6.25 Gbps			UI

7.5.4 1GbE (1000BASE-T)

The following table describes 1GbE (1000BASE-T).

Table 61 • 1GbE (1000BASE-T)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

The following table describes 1GbE (1000BASE-X).

Table 62 • 1GbE (1000BASE-X)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

7.5.5 SGMII and QSGMII

The following table describes SGMII.

Table 63 • SGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps		0.24	UI
Receiver jitter tolerance	1.25 Gbps	0.749		UI

The following table describes QSGMII.

Table 64 • QSGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps		0.3	UI
Receiver jitter tolerance	5.0 Gbps	0.65		UI

7.5.6 SDI

The following table describes SDI.

Table 65 • SDI

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter				UI
Receiver jitter tolerance				UI

Parameter	Devices	Typ	Max	Unit
UFS UPERM digest run time	MPF100T, TL, TS, TLS			μs
	MPF200T, TL, TS, TLS	33.2	34.9	μs
	MPF300T, TL, TS, TLS	33.2	34.9	μs
	MPF500T, TL, TS, TLS			μs
Factory digest run time	MPF100T, TL, TS, TLS			μs
	MPF200T, TL, TS, TLS	493.6	510.1	μs
	MPF300T, TL, TS, TLS	493.6	510.1	μs
	MPF500T, TL, TS, TLS			μs

1. The entire sNVM is used as ROM.
2. Valid for user key 0 through 6.

Note: These times do not include the power-up to functional timing overhead when using digest checks on power-up.

7.6.6 Zeroization Time

The following tables describe zeroization time. A zeroization operation is counted as one programming cycle.

Table 77 • Zeroization Times for MPF100T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1, 4}			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 78 • Zeroization Times for MPF200T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing

Parameter	Type	Max	Unit	Conditions
Time to destroy data in non-volatile memory (non-recoverable) ^{1,4}		ms		One iteration of scrubbing
Time to scrub the fabric data ¹		s		Full scrubbing
Time to scrub the pNVM data (like new) ^{1,2}		s		Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1,3}		s		Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ¹		s		Full scrubbing
Time to verify ⁵		s		

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

7.6.7 Verify Time

The following tables describe verify time.

Table 81 • Standalone Fabric Verify Times

Parameter	Devices	Max	Unit
Standalone verification over JTAG	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	53 ¹	s
	MPF300T, TL, TS, TLS	90 ¹	s
	MPF500T, TL, TS, TLS		s
Standalone verification over SPI	MPF100T, TL, TS, TLS		s
	MPF200T, TL, TS, TLS	37 ²	s
	MPF300T, TL, TS, TLS	55 ²	s
	MPF500T, TL, TS, TLS		s

1. Programmer: FlashPro5, TCK 10 MHz; PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.
2. SmartFusion2 with MSS running at 100 MHz, MSS_SPI_0 port running at 6.67 MHz. DirectC version 4.1.

Notes:

- Standalone verify is limited to 2,000 total device hours over the industrial –40 °C to 100 °C temperature.
- Use the digest system service, for verify device time more than 2,000 hours.
- Standalone verify checks the programming margin on both the P and N gates of the push-pull cell.
- Digest checks only the P side of the push-pull gate. However, the push-pull gates work in tandem. Digest check is recommended if users believe they will exceed the 2,000-hour verify time specification.

Table 82 • Verify Time by Programming Hardware

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF100T, TL, TS, TLS						
MPF200T, TL, TS, TLS	9	67	53			s
MPF300T, TL, TS, TLS	14	95	90			s

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Secure NVM read	T _{SNVM_Rd}	18H				Note 1
Digital signature service raw	T _{SIG_RAW}	19H	174	187	ms	
Digital signature service DER	T _{SIG_DER}	1AH	174	187	ms	
Reserved		1BH–1FH				
PUF emulation	T _{Challenge}	20H	1.8	2.0	ms	
Nonce service	T _{Nonce}	21H	1.2	1.4	ms	
Bitstream authentication	T _{BIT_AUTH}	22H				Note 4
IAP Image authentication	T _{IAP_AUTH}	23H				Note 4
Reserved		26H–3FH				
In application programming by index	T _{IAP_Prg_Index}	42H				Note 2
In application programming by SPI address	T _{IAP_Prg_Addr}	43H				Note 2
In application verify by index	T _{IAP_Ver_Index}	44H				Note 5
In application verify by SPI address	T _{IAP_Ver_Addr}	45H				Note 5
Auto update	T _{AutoUpdate}	46H				Note 2
Digest check	T _{Digest_chk}	47H				Note 3

1. See [sNVM Read/Write Characteristics \(see page 58\)](#).
2. See [SPI Master Programming Time \(see page 52\)](#).
3. See [Digest Times \(see page 54\)](#).
4. See [Authentication Services Time \(see page 58\)](#).
5. See [Verify Services Time \(see page 58\)](#).
6. Throughputs described are measured from SS_REQ assertion to BUSY de-assertion.

7.8

Fabric Macros

This section describes switching characteristics of UJTAG, UJTAG_SEC, USPI, system controller, and temper detectors and dynamic reconfiguration details.

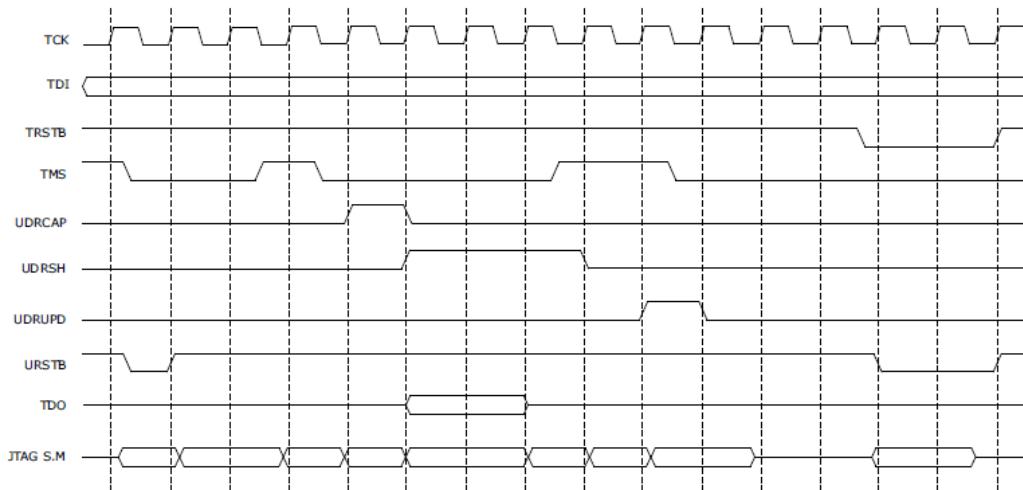
7.8.1

UJTAG Switching Characteristics

The following section describes characteristics of UJTAG switching.

Table 88 • UJTAG Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F _{TCK}			25	MHz	

Figure 3 • UJTAG Timing Diagram

7.8.2 UJTAG_SEC Switching Characteristics

The following table describes characteristics of UJTAG_SEC switching.

Table 89 • UJTAG Security Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	f_{TCK}				MHz	

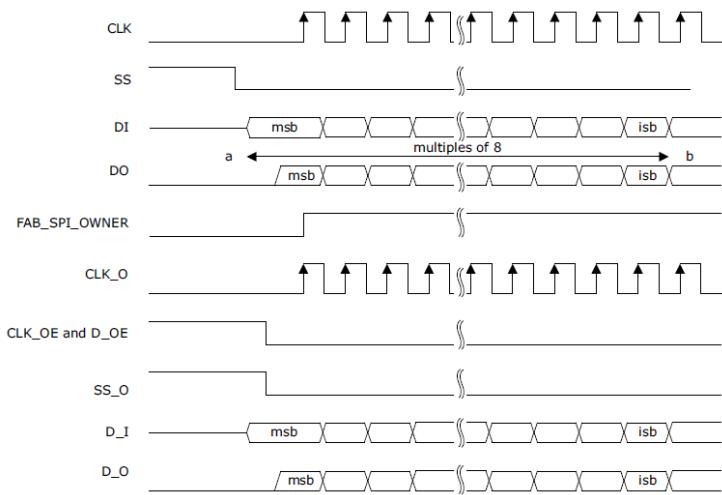
7.8.3 USPI Switching Characteristics

The following section describes characteristics of USPI switching.

Table 90 • SPI Macro Interface Timing Characteristics

Parameter	Symbol	$V_{DDI} = 3.3\text{ V}$ Max	$V_{DDI} = 2.5\text{ V}$ Max	$V_{DDI} = 1.8\text{ V}$ Max	$V_{DDI} = 1.5\text{ V}$ Max	$V_{DDI} = 1.2\text{ V}$ Max	Unit
Propagation delay from the fabric to pins ¹	TPD_MOSI	0.8	1	1.2	1.4	1.6	ns
	TPD_MISO	3.5	3.75	4	4.25	4.5	ns
	TPD_SS	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK	3.5	3.75	4	4.25	4.5	ns
	TPD_MOSI_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SS_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK_OE	3.5	3.75	4	4.25	4.5	ns

- Assumes CL of the relevant I/O standard as described in the input and output delay measurement tables.

Figure 4 • USPI Switching Characteristics

7.8.4 Tamper Detectors

The following section describes tamper detectors.

Table 91 • ADC Conversion Rate

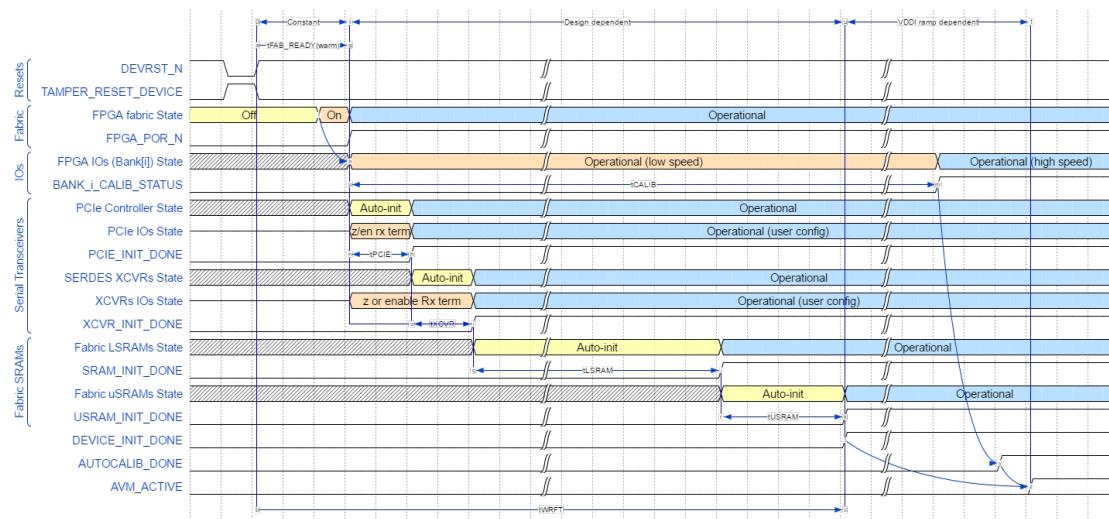
Parameter	Description	Min	Typ ¹	Max
T _{CONV1}	Time from enable changing from zero to non-zero value to first conversion completes. Minimum value applies when POWEROFF = 0.	420 μ s		470 μ s
T _{CONVN}	Time between subsequent channel conversions.		480 μ s	
T _{SETUP}	Data channel and output to valid asserted. Data is held until next conversion completes, that is >480 μ s.	0 ns		
T _{VALID²}	Width of the valid pulse.	1.625 μ s		2 μ s
T _{RATE}	Time from start of first set of conversions to the start of the next set. Can be considered as the conversion rate. Is set by the conversion rate parameter.	480 μ s	Rate \times 32 μ s	8128 μ s

1. Min, typ, and max refer to variation due to functional configuration and the raw TVS value. The actual internal correction time will vary based on the raw TVS value.
2. The pulse width varies depending on the time taken to complete the internal calibration multiplication, this can be up to 375 ns.

Note: Once the TVS block is active, the enable signal is sampled 25 ns before the falling edge of valid. The next enabled channel in the sequence 0-1-2-3 is started; that is, if channel 0 has just completed and only channels 0 and 3 are enabled, the next channel will be 3. When all the enabled channels in the sequence 0-1-2-3 are completed, the TVS waits for the conversion rate timer to expire. The enable signal may be changed at any time if it changes to 4'b0000 while valid is asserted (and 25 ns before valid is de-asserted), then no further conversions will be started.

Table 92 • Temperature and Voltage Sensor Electrical Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensing range	-40		125	°C	
Temperature sensing accuracy	-10		10	°C	

Figure 6 • Warm Reset Timing

7.9.3 Power-On Reset Voltages

7.9.3.1 Main Supplies

The start of power-up to functional time (T_{PUFT}) is defined as the point at which the latest of the main supplies (VDD, VDD18, VDD25) reach the reference voltage levels specified in the following table. This starts the process of releasing the reset of the device and powering on the FPGA fabric and IOs.

Table 97 • POR Ref Voltages

Supply	Power-On Reset Start Point (V)	Note
VDD	0.95	Applies to both 1.0 V and 1.05 V operation.
VDD18	1.71	
VDD25	2.25	

7.9.3.2 I/O-Related Supplies

For the I/Os to become functional (for low speed, sub 400 MHz operation), the (per-bank) I/O supplies (VDDI, VDDAUX) must reach the trip point voltage levels specified in the following table and the main supplies above must also be powered on.

Table 98 • I/O-Related Supplies

Supply	I/O Power-Up Start Point (V)
VDDI	0.85
VDDAUX	1.6

There are no sequencing requirements for the power supplies. However, VDDI3 must be valid at the same time as the main supplies. The other IO supplies (VDDI, VDDAUX) have no effect on power-up of FPGA fabric (that is, the fabric still powers up even if the IO supplies of some IO banks remain powered off).